

RJF0604JPD

Silicon N Channel MOS FET Series Power Switching

R07DS0583EJ0100
Rev.1.00
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Description

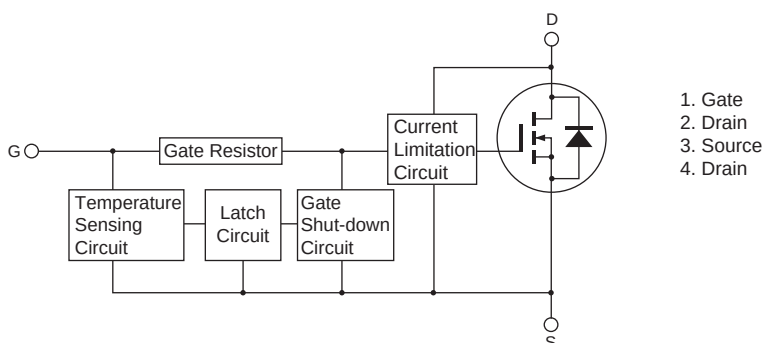
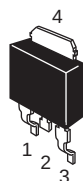
This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc..

Features

- Logic level operation (5 V Gate drive).
- Built-in the over temperature shut-down circuit.
- High endurance capability against to the short circuit.
- Latch type shut down operation (need 0 voltage recovery).
- Built-in the current limitation circuit.
- Power supply voltage applies 12 V and 24 V.
- AEC-Q101 Compliant

Outline

RENESAS Package code: PRSS0004ZD-C
(Package name: DPAK (S))



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	16	V
Gate to source voltage	V_{GSS}	-2.5	V
Drain current	I_D ^{Note 3}	5	A
Body-drain diode reverse drain current	I_{DR} ^{Note 2}	5	A
Avalanche current	I_{AP} ^{Note 2}	(4.7)	A
Avalanche energy	E_{AR} ^{Note 2}	(94.7)	mJ
Channel dissipation	P_{ch} ^{Note 1}	30	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. Value at $T_c = 25^\circ\text{C}$
 2. $T_{ch} = 25^\circ\text{C}$, $R_g \geq 50 \Omega$
 3. It provides by the current limitation lower bound value.

Typical Operation Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input voltage	V _{IH}	3.5	—	—	V	
	V _{IL}	—	—	1.2	V	
Input current (Gate non shut down)	I _{IH1}	—	—	100	μA	V _i = 8 V, V _{DS} = 0
	I _{IH2}	—	—	50	μA	V _i = 3.5 V, V _{DS} = 0
	I _{IL}	—	—	1	μA	V _i = 1.2 V, V _{DS} = 0
Input current (Gate shut down)	I _{IH(sd)1}	—	0.8	—	mA	V _i = 8 V, V _{DS} = 0
	I _{IH(sd)2}	—	0.35	—	mA	V _i = 3.5 V, V _{DS} = 0
Shut down temperature	T _{sd}	—	175	—	°C	Channel temperature
Gate operation voltage	V _{op}	3.5	—	12	V	
Drain current (Current limitation value)	I _{D limit}	(5)	—	—	A	V _{GS} = 5 V, V _{DS} = 10 V ^{Note 4}

Note; 4. Pulse test

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain current	I _{D1}	—	—	(17)	A	V _{GS} = 3.5 V, V _{DS} = 10 V ^{Note 5}
	I _{D2}	—	—	(10)	mA	V _{GS} = 1.2 V, V _{DS} = 10 V
	I _{D3}	(5)	—	—	A	V _{GS} = 5 V, V _{DS} = 10 V ^{Note 5}
Drain to source breakdown voltage	V _{(BR)DSS}	60	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR)GSS}	16	—	—	V	I _G = 800 μA, V _{DS} = 0
	V _{(BR)GSS}	-2.5	—	—	V	I _G = -100 μA, V _{DS} = 0
Gate to source leak current	I _{GSS1}	—	—	100	μA	V _{GS} = 8 V, V _{DS} = 0
	I _{GSS2}	—	—	50	μA	V _{GS} = 3.5 V, V _{DS} = 0
	I _{GSS3}	—	—	1	μA	V _{GS} = 1.2 V, V _{DS} = 0
	I _{GSS4}	—	—	-100	μA	V _{GS} = -2.4 V, V _{DS} = 0
Input current (shut down)	I _{GS(OP)1}	—	0.8	—	mA	V _{GS} = 8 V, V _{DS} = 0
	I _{GS(OP)2}	—	0.35	—	mA	V _{GS} = 3.5 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS1}	—	—	10	μA	V _{DS} = 32 V, V _{GS} = 0
	I _{DSS2}	—	—	(10)	μA	V _{DS} = 60 V, V _{GS} = 0, Ta = 110°C
Gate to source cutoff voltage	V _{GS(off)}	(1.2)	—	(2.4)	V	V _{DS} = 10 V, I _D = 1 mA
Forward transfer admittance	y _{fs}	(4)	(7.6)	—	S	I _D = 2.5 A, V _{DS} = 10 V ^{Note 5}
Static drain to source on state resistance	R _{DS(on)}	—	(76)	100	mΩ	I _D = 2.5 A, V _{GS} = 4 V ^{Note 5}
	R _{DS(on)}	—	(51)	(75)	mΩ	I _D = 2.5 A, V _{GS} = 10 V ^{Note 5}
Output capacitance	C _{oss}	—	(280)	—	pF	V _{DS} = 10 V, V _{GS} = 0, f = 1MHz
Turn-on delay time	t _{d(on)}	—	(4.1)	—	μs	V _{GS} = 5 V, I _D = 2.5 A, R _L = 12 Ω
Rise time	t _r	—	(16)	—	μs	
Turn-off delay time	t _{d(off)}	—	(2.5)	—	μs	
Fall time	t _f	—	(3.1)	—	μs	
Body-drain diode forward voltage	V _{DF}	—	(0.84)	—	V	I _F = 5 A, V _{GS} = 0
Body-drain diode reverse recovery time	t _{rr}	—	(100)	—	ns	I _F = 5 A, V _{GS} = 0 di/dt = 50 A/μs
Over load shut down operation time ^{Note 6}	t _{os1}	—	(1.2)	—	ms	V _{GS} = 5 V, V _{DD} = 16 V
	t _{os2}	—	(0.7)	—	ms	V _{GS} = 5 V, V _{DD} = 24 V

Notes: 5. Pulse test

6. Including the junction temperature rise of the over loaded condition.

Unit: mm

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